



30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

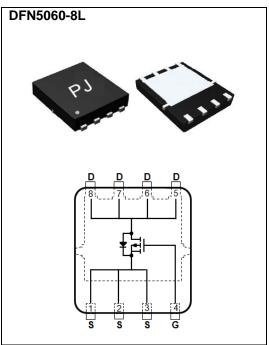
-60 A

Features

- R_{DS(ON)}, V_{GS}@-10V,I_D@-10A<8.5mΩ
- R_{DS(ON)}, V_{GS}@-4.5V,I_D@-8A<14mΩ
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	-60	А	
	T _C =100°C		-38		
Pulsed Drain Current ^(Note 1)	T _C =25°C	I _{DM}	-240	İ	
Power Dissipation	T _C =25°C	Po	63	W	
	T _C =100°C		25		
Continuous Drain Current	T _A =25°C	I _D	-11	А	
	T _A =70°C		-8.8	Α	
Power Dissipation	T _A =25°C	5	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		T_J , T_{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{ heta JC}$	2.0	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1.0	-1.5	-2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-10A	-	7.1	8.5	mΩ	
		V_{GS} =-4.5V, I_{D} =-8A	-	10	14		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	-1.0	uA	
Gate-Source Leakage Current	I _{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	Q_g	\/ 45\/ L 40A	-	27	-	nC	
Gate-Source Charge	Q_gs	V _{DS} =-15V, I _D =-10A, V _{GS} =-4.5V ^(Note 1,2)	-	8.4	-		
Gate-Drain Charge	Q_gd	V _{GS} =-4.5 V	-	8.7	-		
Input Capacitance	Ciss	V _{DS} =-15V, V _{GS} =0V,	-	3228	-	pF	
Output Capacitance	Coss	v _{DS} =-15V, v _{GS} =UV, f=1.0MHZ	-	396	-		
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	254	-		
Turn-On Delay Time	td _(on)	\\\ 45\\\D\ 4A	-	10	-		
Turn-On Rise Time	V _{DS} =-15V,ID=-1A,		-	13	-	200	
Turn-Off Delay Time	td _(off)	V_{GS} =-10V, R_{G} =6 Ω (Note 1,2)	-	111	-	ns	
Turn-Off Fall Time	t _f		-	51	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	ı		-	-	-60	А	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =-1A,V _{GS} =0V	-	-0.7	-1	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

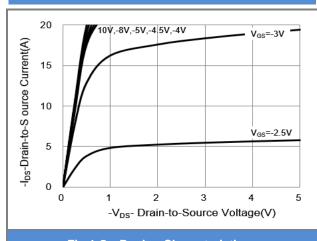


Fig.1 On-Region Characteristics

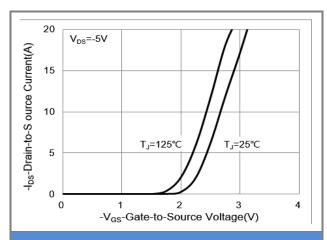


Fig.2 Transfer Characteristics

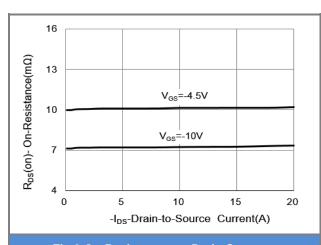


Fig.3 On-Resistance vs. Drain Current

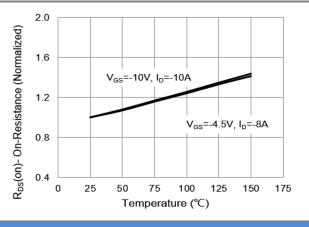


Fig.4 On-Resistance vs. Junction temperature

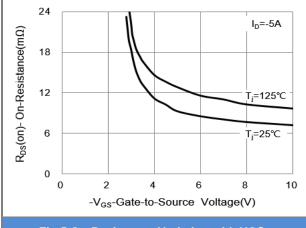


Fig.5 On-Resistance Variation with VGS.

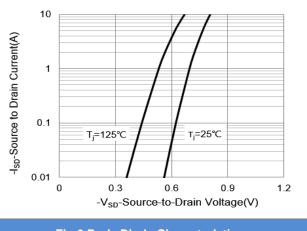


Fig.6 Body Diode Characteristics





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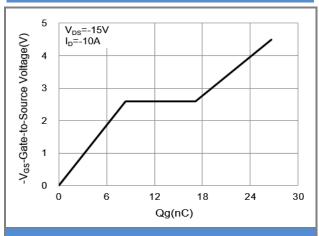


Fig.7 Gate-Charge Characteristics

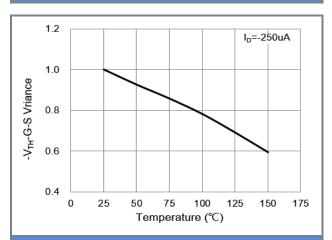


Fig.9 Threshold Voltage Variation with Temperature.

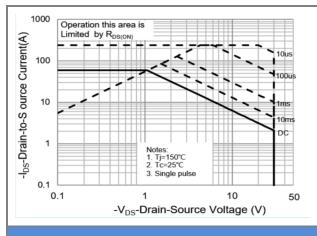


Fig.11 Maximum Safe Operating Area

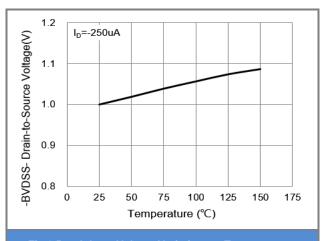


Fig.8 Breakdown Voltage Variation vs. Temperature

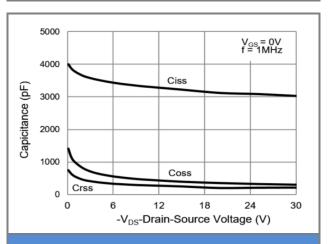


Fig.10 Capacitance vs. Drain-Source Voltage.





TYPICAL CHARACTERISTIC CURVES

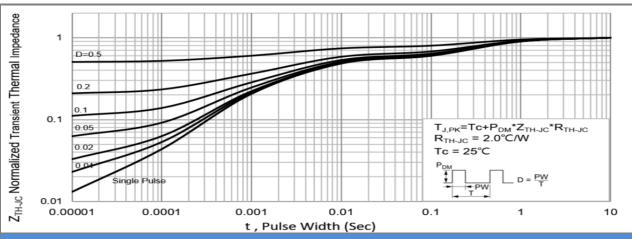


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

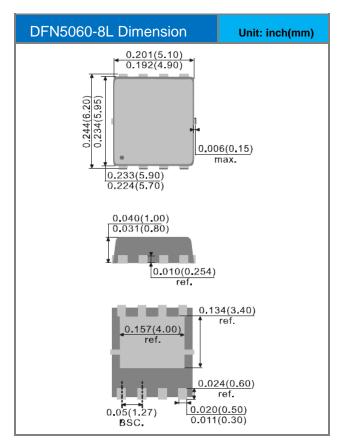


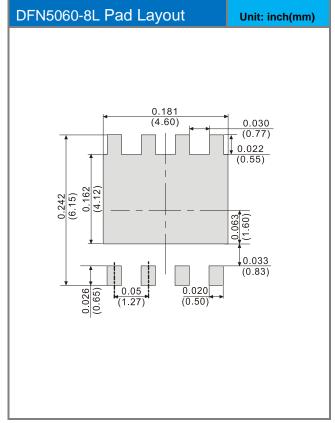


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5423_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5423	Halogen free	

Packaging Information & Mounting Pad Layout









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